

4V Drive Pch + Pch MOSFET

QS8J5

Structure

Silicon P-channel MOSFET

Features

- 1) Low on-resistance.
- 2) High power package(TSMT8).
- 3) Low voltage drive(4V drive).

Application

Switching

Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
QS8J5		0

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	-30	V	
Gate-source voltage		V_{GSS}	±20	V	
Drain current	Continuous	I _D	±5	Α	
	Pulsed	I _{DP} *1	±20	Α	
Source current (Body Diode)	Continuous	l _s	-1	Α	
	Pulsed	I _{sp} *1	-20	Α	
Power dissipation		P _D *2	1.5	W / TOTAL	
		т Б -	1.25	W / ELEMENT	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

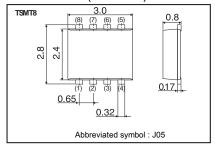
^{*1} Pw≤10µs, Duty cycle≤1%

Thermal resistance

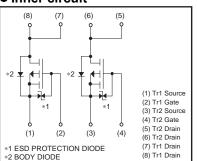
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)	83.3	°C / W /TOTAL
Charmer to ambient		100	°C / W /ELEMENT

^{*} Each terminal mounted on a ceramic board.

Dimensions (Unit : mm)



• Inner circuit



^{*2} Each terminal mounted on a ceramic board.

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● Electrical characteristics (Ta = 25°C)

<It is the same ratings for Tr1 and Tr2.>

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	-	-	±10	μA	$V_{GS}=\pm20V$, $V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	-30	-	-	V	$I_D = -1 \text{mA}, V_{GS} = 0 \text{V}$
Zero gate voltage drain current	I _{DSS}	1	-	-1	μA	V_{DS} =-30V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	-1.0	1	-2.5	٧	V_{DS} =-10V, I_{D} =-1mA
2	*	1	28	39		I _D =-5A, V _{GS} =-10V
Static drain-source on-state resistance	R _{DS (on)}	1	40	56	mΩ	$I_D = -2.5A, V_{GS} = -4.5V$
		1	45	63		I _D =-2.5A, V _{GS} =-4V
Forward transfer admittance	I Y _{fs} I*	3	-	-	S	I _D =-5A, V _{DS} =-10V
Input capacitance	C _{iss}	1	1100	1	pF	V _{DS} =-10V
Output capacitance	C _{oss}	1	150	1	pF	V _{GS} =0V
Reverse transfer capacitance	C_{rss}	1	130	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	1	9	1	ns	I _D =-2.5A, V _{DD} ≒-15V
Rise time	t _r *	1	40	ı	ns	V _{GS} =-10V
Turn-off delay time	t _{d(off)} *	-	90	-	ns	R <u></u> ≒6Ω
Fall time	t _f *	1	55	-	ns	R_G =10 Ω
Total gate charge	Q _g *	-	10.0	-	nC	I _D =–5A, V _{DD} ≒–15V
Gate-source charge	Q _{gs} *	-	3.6	-	nC	V _{GS} =-5V
Gate-drain charge	Q _{gd} *	-	3.0	-	nC	R _L ≒3Ω, R _G =10Ω

^{*}Pulsed

●Body diode characteristics (Source-Drain) (Ta = 25°C)

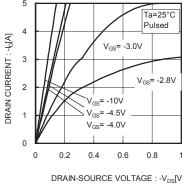
<It is the same ratings for Tr1 and Tr2.>

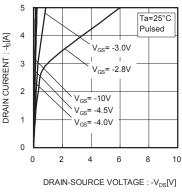
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	-	-	-1.2	V	I_s =-5A, V_{GS} =0V

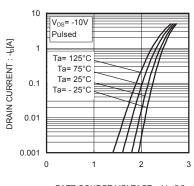
^{*}Pulsed

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Electrical characteristic curves



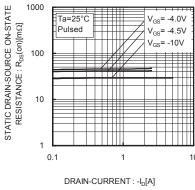


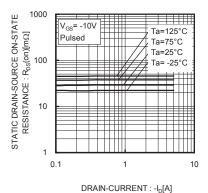


DRAIN-SOURCE VOLTAGE: -VDS[V] Fig.1 Typical Output Characteristics($\ensuremath{\mathbb{I}}$)

Fig.2 Typical Output Characteristics(${\rm I\hspace{-.1em}I}$)

GATE-SOURCE VOLTAGE: -VGS[V] Fig.3 Typical Transfer Characteristics





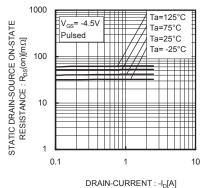
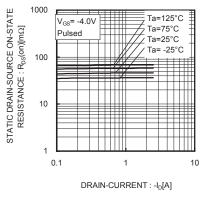


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current([)

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current(${\rm II}$)

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(Ⅲ)



FORWARD TRANSFER ADMITTANCE: |Yfs| [S] 100 V_{DS}= -10V Pulsed 10 Ta=25°C Ta=75°C Ta=125°C 0.1 0.01 0.1 10 DRAIN-CURRENT : -I_D[A]

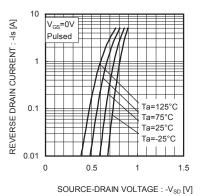
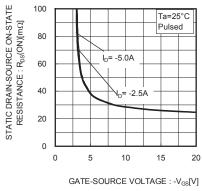


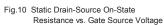
Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

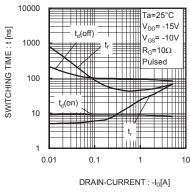
Fig.8 Forward Transfer Admittance vs. Drain Current

Fig.9 Reverse Drain Current vs. Sourse-Drain Voltage

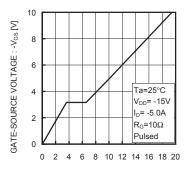
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.11 Switching Characteristics



TOTAL GATE CHARGE : Qg [nC]
Fig.12 Dynamic Input Characteristics

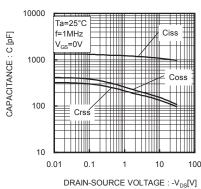


Fig.13 Typical Capacitance vs. Drain-Source Voltage

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Measurement circuits

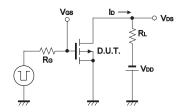
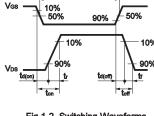


Fig.1-1 Switching Time Measurement Circuit



Pulse Width

Fig.1-2 Switching Waveforms

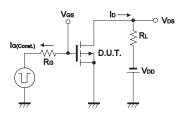


Fig.2-1 Gate Charge Measurement Circuit

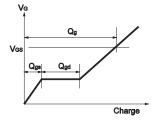


Fig.2-2 Gate Charge Waveform

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